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(54) **Title:** METHOD FOR MANUFACTURING CMP COMPOSITION AND APPLICATION THEREOF

(57) **Abstract:** Provided is a process for the manufacture of semiconductor devices comprising the chemical mechanical polishing of borophosphosilicate glass (BPSG) material in the presence of a chemical mechanical polishing (CMP) composition which comprises: (A) inorganic particles, organic particles, or a mixture or composite thereof, (B) at least one type of anionic phosphate or phosphonate as dispersing agent or charge reversal agent, (C) at least one type of surfactant, and (D) an aqueous medium.



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